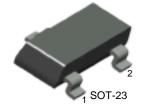


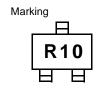
KSR1110

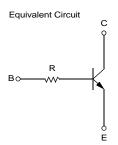
Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R=10KΩ)
- Complement to KSR2110



1. Base 2. Emitter 3. Collector





NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	100	mA
P _C	Collector Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	40			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _E =1mA, I _B =0	40			V
I _{CBO}	Collector Cut-off Current	V_{CB} =30V, I_E =0			0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} =5V, I _C =1mA	100		600	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA			0.3	V
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0 f=1MHz		3.7		pF
f _T	Current Gain Bandwidth Product	V _{CE} =10V, I _C =5mA		250		MHz
R	Input Resistor		7	10	13	ΚΩ

Typical Characteristics

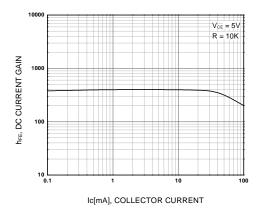


Figure 1. DC current Gain

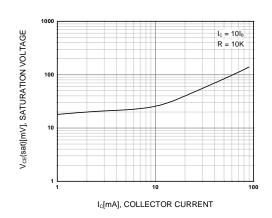


Figure 2. Collector-Emitter Saturation Voltage

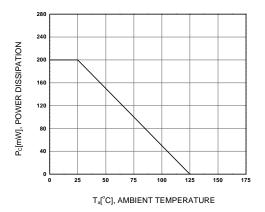
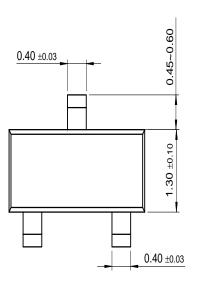
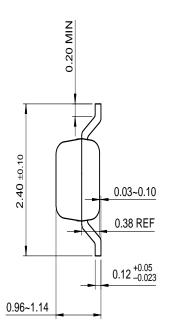


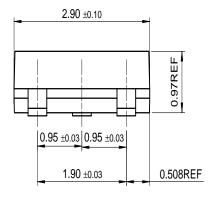
Figure 3. Power Derating

Package Demensions

SOT-23







Dimensions in Millimeters

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